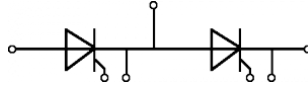


## Thyristor module PSKT 332M

$I_{T(RMS)} = 2 \times 518 \text{ A}$   
 $I_{T(AV)} = 2 \times 330 \text{ A}$   
 $V_{RRM} = 800-1800 \text{ V}$

### Preliminary Data Sheet



$V_{RSM}$ V	$V_{RRM}$ V	Type
900	800	PSKT 332M/08
1100	1000	PSKT 332M/10
1300	1200	PSKT 332M/12
1500	1400	PSKT 332M/14
1700	1600	PSKT 332M/16
1900	1800	PSKT 332M/18

Symbol	Test Conditions	Maximum Ratings		
$I_{T(RMS)}$	$T_{VJ} = 125^\circ\text{C}$	half sine	518	A
$I_{T(AV)}$	$T_C = 85^\circ\text{C}$		330	A
$I_{TSM}$	$T_{VJ} = 125^\circ\text{C}$	$t = 10 \text{ ms}$	half sine	9100 A
$\int i^2 dt$	$T_{VJ} = 125^\circ\text{C}$	$t = 10 \text{ ms}$	half sine	414 $\text{A}^2 \text{ s} \cdot 10^3$
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$	$t_r \leq 0,5 \mu\text{s}$	gate source 1,5A	200 $\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$	$V_{DM} = 2/3 V_{DRM}$		1000 $\text{V}/\mu\text{s}$
$T_{VJ}$		-40 ... + 125		$^\circ\text{C}$
$T_{VJM}$		125		$^\circ\text{C}$
$T_{stg}$		-40 ... + 125		$^\circ\text{C}$
$V_{ISOL}$	50 HZ, RMS $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$	min. 3000	$\text{V} \sim$
$M_d$	Terminal connection torque Mounting torque	(M10) (M6)	12,0 6,0	Nm
Weight	typ.		820	g

### Features

- Isolated mounting base 3000V~
- Pressure contact technology with increased power cycling capability

### Applications

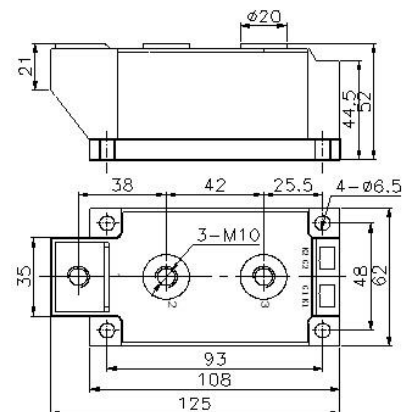
- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

### Advantages

- Easy to mount
- Space and weight savings
- Improved temperature and power cycling capability

### Package, style and outline

Dimensions in mm (1mm = 0.0394")



Symbol	Test Conditions	Characteristic Value		
$I_{RRM}; I_{DRM}$	$V_R = V_{RRM}$ $V_D = V_{DRM}$	$T_{VJ} = 125^\circ\text{C}$	$\leq$	25 mA
$V_{TM}$	$I_{TM} = 750 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$	$\leq$	1,45 V
$V_{TO}$	For power-loss calculations only			0,8 V
$r_T$	$T_{VJ} = 125^\circ\text{C}$			0,53 $\text{m}\Omega$
$I_{GT}$				30-180 mA
$V_{GT}$	$V_A = 12 \text{ V}$ $I_A = 1 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$		1,0-2,5 V
$I_H$				20-180 mA
$V_{GT}$	$V_{DM} = 2/3 V_{DRM}$	$T_{VJ} = 125^\circ\text{C}$		0,2 V
$R_{th(j-c)}$	Per chip; Single side cooled			0,12 $^\circ\text{C}/\text{W}$